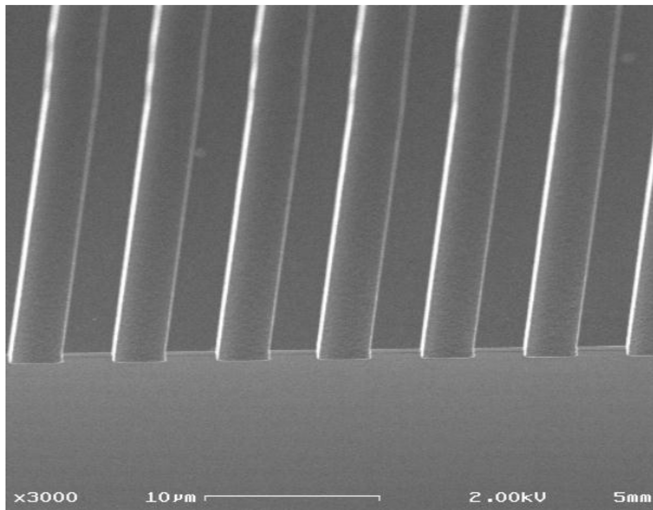
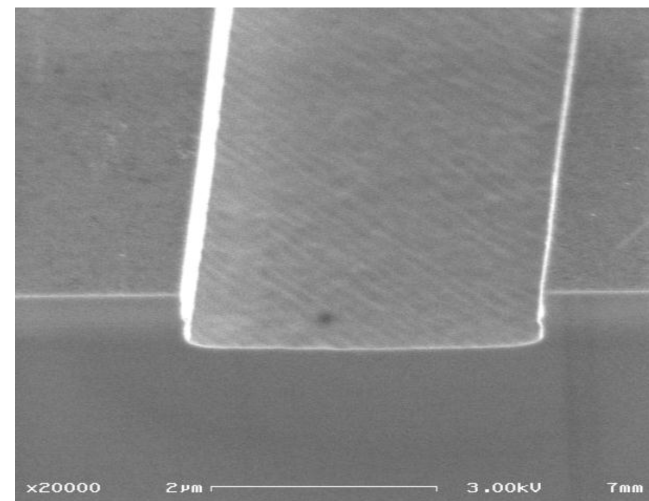
AlGaAs Trenches

Substrate:	AlGaAs
Chemistry:	BCl3, Cl2
Mask:	Photoresist
Selectivity:	> 3:1
Etch rate:	0.7 um/min

BCl3 flow:	22.5 sccm
Cl2 flow:	7.5 sccm
Pressure:	3 mTorr
ICP Power:	500 W
RF Bias:	100 W
Temperature:	20 °C





clean & smooth etch surface, > 85degree side wall angle, good selectivity to photo resist